

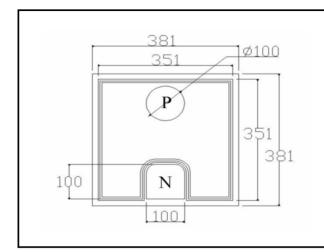
# ELC-505-34

# LED Chip vis

ELC-505-34

Rev. 01 aus 2011

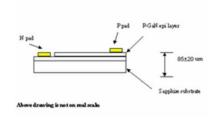
Radiation	Туре	Electrodes
green		P + N up



#### Description

-Sustrate: Saphire, epitaxial layer: GaN based Material

-N bonding pad electrode: Au alloy-P bonding pad electrode: Au alloy



### **Maximum Ratings**

T<sub>amb</sub>= 25℃, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Тур	Max	Unit
Forward current (DC)		I <sub>F</sub>			20	mA
Peak forward current	t <sub>p</sub> ≤ 50 μs,	I <sub>FM</sub>			100	mA

# **Optical and Electrical Characteristics**

T<sub>amb</sub>= 25℃, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Тур	Max	Unit
Forward voltage	I <sub>F</sub> =20mA	V <sub>F</sub>		3.3	3.5	V
Reverse current	V <sub>R</sub> =5V	I <sub>R</sub>			1	μΑ
Dominant wavelength	I <sub>F</sub> =20mA	$\lambda_{p}$	502	505	508	nm
Full width at half maximum	I <sub>F</sub> =20mA	Δλ		40		nm
Luminous intensity 1	I <sub>F</sub> =20mA	lv	300		500	mcd

#### **Packing**

Chips on adhesive film with wire-bond side top



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